2N5484, 2N5485, 2N5486

N-Channel Silicon Junction Field-Effect Transistor

- VHF/UHF Amplifiers

Absolute maximum ratings at T_A = 25°C

Reverse Gate Source Voltage	– 25 V
Reverse Gate Drain Voltage	– 25 V
Continuous Device Power Dissipation	360 mW
Power Derating	3.27 mW/°C

At 25°C free air temperature: Static Electrical Characteristics		2N5484		2N5485		2N5486		Process NJ26		
		Min	Max	Min	Max	Min	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 25		– 25		– 25		V	I_G = 1µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}		– 1		– 1		– 1	nA	V_{GS} = – 20V, V_{DS} = ØV	
			– 0.2		– 0.2		– 0.2	µA	V_{GS} = – 20V, V_{DS} = ØV	T_A = 100°C
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 0.3	– 3	– 0.5	– 4	– 2	– 6	V	V_{DS} = 15V, I_D = 10 nA	
Drain Saturation Current (Pulsed)	I_{DSS}	1	5	4	10	8	20	mA	V_{DS} = 15V, V_{GS} = ØV	
Dynamic Electrical Characteristics										
Forward Transconductance	$R_{e(Yfs)}$	2500						µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
				3000		3500		µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Forward Transadmittance	Y_{fs}	3000	6000	3500	7000	4000	8000	µS	V_{DS} = 15V, V_{GS} = ØV	f = 1 kHz
Input Admittance	$R_{e(Yis)}$		100					µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
					1000		1000	µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Output Conductance	$R_{e(Yos)}$		75					µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
					100		100	µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Output Admittance	Y_{os}		50		60		75	µS	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Input Capacitance	C_{iss}		5		5		5	pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Reverse Transfer Capacitance	C_{rss}		1		1		1	pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Output Capacitance	C_{oss}		2		2		2	pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz

TO-226AA Package
Dimensions in Inches (mm)

Pin Configuration
1 Drain, 2 Source, 3 Gate

Surface Mount
SMP5484, SMP5485, SMP5486

InterFET Corporation
1000 N. Shiloh Road, Garland, TX 75042
(972) 487-1287 FAX (972) 276-3375